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# Ultrasensitive and stable X-ray detection using zero-dimensional lead-free perovskites

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## ABSTRACT

Sensitive and reliable X-ray detectors are essential for medical radiography, industrial inspection and security screening. Lowering the radiation dose allows reduced health risks and increased frequency and fidelity of diagnostic technologies for earlier detection of disease and its recurrence. Three-dimensional (3D) organic-inorganic hybrid lead halide perovskites are promising for direct X-ray detection – they show improved sensitivity compared to conventional X-ray detectors. However, their high and unstable dark current, caused by ion migration and high dark carrier concentration in the 3D hybrid perovskites, limits their performance and long-term operation stability. Here we report ultrasensitive, stable X-ray detectors made using zero-dimensional (0D) methylammonium bismuth iodide perovskite (MA<sub>3</sub>Bi<sub>2</sub>I<sub>9</sub>) single crystals. The 0D crystal structure leads to a high activation energy ( $E_a$ ) for ion migration (0.46 eV) and is also accompanied by a low dark carrier concentration ( $\sim 10^6 \text{ cm}^{-3}$ ). The X-ray detectors exhibit sensitivity of  $10,620 \mu\text{C Gy}_{\text{air}}^{-1} \text{ cm}^{-2}$ , a limit of detection (LoD) of  $0.62 \text{ nGy}_{\text{air}} \text{ s}^{-1}$ , and stable operation even under high applied biases; no deterioration in detection performance was observed following sensing of an integrated X-ray irradiation dose of  $\sim 23,800 \text{ mGy}_{\text{air}}$ , equivalent to  $> 200,000$  times the dose required for a single commercial X-ray chest radiograph. Regulating the ion migration channels and decreasing the dark carrier concentration in perovskites provide routes for stable and ultrasensitive X-ray detectors.

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## 1. Introduction

X-ray detection is widely applied in medical diagnostics and security screening. These applications require sensitive X-ray detectors that enable decreasing the dose required in order to reduce health risks [1,2]. However, the sensitivity and minimum detectable dose rate, or limit of detection (LoD) of X-ray radiological instruments, is limited today by the materials used in the detectors [3]. The sensitivities of direct-conversion amorphous selenium (a-Se) detectors, and of indirect-conversion thallium-doped cesium iodide (CsI:Tl) detectors, two dominant X-ray detectors, are lower than  $400 \mu\text{C Gy}_{\text{air}}^{-1} \text{ cm}^{-2}$  [4–6].

Enhancing the X-ray sensitivity and lowering the LoD of direct-conversion X-ray detectors has been explored extensively [5]. Organic-inorganic hybrid lead halide perovskites, widely investigated in solar energy conversion, are also promising materials for X-ray detection applications because of their high attenuation coefficients, large mobility-lifetime ( $\mu\tau$ ) products, and their fabrication via solution processing [7–10]. An X-ray sensitivity exceeding  $10,000 \mu\text{C Gy}_{\text{air}}^{-1} \text{ cm}^{-2}$  and achieving a LoD of  $36 \text{ nGy}_{\text{air}} \text{ s}^{-1}$  has been achieved using 3D hybrid perovskite detectors – and both the sensitivity and LoD are superior to those of traditional X-ray detectors [2,11]. However, long-term operational stability in lead halide perovskite X-ray detectors remains to be achieved. Ion migration in 3D hybrid perovskites causes instability and dark current drift, the latter preventing achievement of a low LoD [12,13]. It remains an open problem to achieve X-ray sensitive materials that simultaneously provide high sensitivity, low LoD, and stable detector operation.

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We posited that disconnecting the inorganic octahedral units in hybrid perovskites could beneficially disrupt ion migration channels. The OD structure, in which the inorganic octahedral units are disconnected in all directions, enables this goal. OD compounds also provide more localized electronic structures, which can decrease the dark carrier concentration compared to in 3D or 2D counterparts [14,15]. Suppressing ion migration and lowering dark carrier concentration enables the needed combination of high sensitivity, low LoD, and stable operation.

Pb-based perovskites add a further regulatory impediment to adoption [16–20]. Bismuth (Bi) is considered a promising candidate to replace Pb: it is not subject to the same RoHS regulations, yet also has a high atomic number [21,22]. Here we report ultrasensitive and stable X-ray detectors enabled by the utilization of solution-processed zero-dimensional (OD) lead-free MA<sub>3</sub>Bi<sub>2</sub>I<sub>9</sub> single crystals, which shows suppressed ion migration (activation energy for ion migration,  $E_a = 0.46$  eV), a dark carrier concentrations of  $\sim 10^6$  cm<sup>-3</sup> and a Hall mobility of 70 cm<sup>2</sup> V<sup>-1</sup> s<sup>-1</sup>. We report X-ray detectors with a high sensitivity of 10,620  $\mu$ C Gy<sub>air</sub><sup>-1</sup> cm<sup>-2</sup> and an LoD of 0.62 nGy<sub>air</sub> s<sup>-1</sup>. The LoD achieved herein is  $\sim 20$  times lower than the lowest LoD reported in literature (see Table S1). The OD perovskite X-ray detectors exhibit stable operation even under high applied biases up to 120 V. No deterioration in detection performance was observed following an X-ray irradiation dose of  $\sim 23,800$  mGy<sub>air</sub> (under bias of 50 V for 1091.3 mGy<sub>air</sub> and 100 V for 22,767.2 mGy<sub>air</sub>), equivalent to  $> 200,000$  times of the dose used in acquiring commercial X-ray chest radiographs.

## 2. Experimental

### 2.1. Materials

The materials used were as follows: bismuth triiodide (BiI<sub>3</sub>) (99%, Sigma-Aldrich), methylamine (CH<sub>3</sub>NH<sub>2</sub>) (40% w/w aq. soln., Alfa Aesar), hydriodic acid (HI) (57% w/w aq. soln., Alfa Aesar),  $\gamma$ -butyrolactone (GBL) ( $>99\%$ , Alfa Aesar), and diethyl ether (anhydrous,  $>99\%$ , Alfa Aesar).

### 2.2. Synthesis of methylammonium iodide (MAI)

MAI was prepared by slowly adding hydroiodic acid into methylamine solution under continuous stirring at 0 °C for 3 h. MAI was crystallized by removing the solvent with a rotary evaporator. The MAI powder was then put into a Soxhlet extractor and repeatedly washed with diethyl ether overnight. The white, shiny crystals were dried under vacuum for 24 h and kept in a nitrogen glove box for further use.

### 2.3. Growth of MA<sub>3</sub>Bi<sub>2</sub>I<sub>9</sub> single crystal

First, 3 M MAI and 2 M BiI<sub>3</sub> were dissolved in GBL solution in a vial to keep the molar ratio of MAI to BiI<sub>3</sub> at 3:2. Then, the solution was heated and stirred at 60 °C on a hot plate for 12 h. The mixture was filtered with a PTFE filter (0.45  $\mu$ m) before use. The MA<sub>3</sub>Bi<sub>2</sub>I<sub>9</sub> single crystal was grown using the seed-crystal-assisted constant-temperature evaporation method (SCA-CTEM). MA<sub>3</sub>Bi<sub>2</sub>I<sub>9</sub> single crystal seeds (1–2 mm in size) were obtained by keeping the precursor solution in a glass beaker at 60 °C for 24 h. Then, one crystal seed was placed into the fresh solution, which was heated and kept at 70 °C for a long period of time. A reddish black MA<sub>3</sub>Bi<sub>2</sub>I<sub>9</sub> crystal with a size of  $\sim 27$  mm  $\times$  23 mm  $\times$  13 mm was obtained after 20 days of growth.

### 2.4. Cutting of the MA<sub>3</sub>Bi<sub>2</sub>I<sub>9</sub> single crystal

A large MA<sub>3</sub>Bi<sub>2</sub>I<sub>9</sub> single crystal was cut into slices with different thicknesses using a diamond wire saw (STX-202A, Shenyang Kejing

Auto-Instrument Co., LTD). The diameter of the diamond wire was 0.125 mm. Isopropanol was used as the cooling liquid during the cutting process.

### 2.5. Characterization of materials

Powder XRD measurements of MA<sub>3</sub>Bi<sub>2</sub>I<sub>9</sub> were performed with an Empyrean X-ray diffractometer with Cu  $K_{\alpha}$  radiation (PANalytical, 1°/min). MA<sub>3</sub>Bi<sub>2</sub>I<sub>9</sub> powders were obtained by grinding the single crystal. Humidity aging of the samples was carried out in a glass desiccator with a constant RH of  $\sim 60\%$ . Thermogravimetric analysis (TGA) and differential scanning calorimetry (DSC) measurements were performed on a thermogravimetric analyzer (TGA/DSC 2, Mettler-Toledo, LLC) at a rate of 10 °C min<sup>-1</sup> under a nitrogen atmosphere. UV–vis absorption spectra were recorded on an Evolution™ 201 spectrophotometer (Thermo Fisher Scientific Corporation) in transmission mode using a MA<sub>3</sub>Bi<sub>2</sub>I<sub>9</sub> crystal slice ( $\sim 0.5$  mm).

### 2.6. Hall-effect measurement

A MA<sub>3</sub>Bi<sub>2</sub>I<sub>9</sub> single crystal with a size of 1.6  $\times$  1.6  $\times$  0.6 mm<sup>3</sup> was used for DC field Hall-effect measurement by van der Pauw method under high resistance mode (Lake Shore, 8400 series). Au evaporated on the four corners was used as the electrodes. The excitation current was 10 pA and the excitation magnetic field was 9 kG.

### 2.7. Hole and electron mobilities measured using the time-of-flight (TOF) method

Gold (Au) charge-collecting electrodes with thicknesses of 10 nm and 80 nm were thermally evaporated on opposite sides of the MA<sub>3</sub>Bi<sub>2</sub>I<sub>9</sub> crystals, and the former was used as the semitransparent electrode for light transmission. The thicknesses of the MA<sub>3</sub>Bi<sub>2</sub>I<sub>9</sub> crystals were 0.88 mm and 1.10 mm for the out-of-plane and in-plane samples, respectively. TOF measurements were conducted by illuminating the devices with 6 ns width, 532 nm laser pulses on the 10 nm semitransparent Au electrode. The bias was applied to the sample using a function generator (DS345, Stanford Research Systems) and a Keithley digital source meter (model 2400). The photocurrent was recorded using a low-noise current preamplifier (SR570, Stanford Research Systems).

For hole mobility measurement, a 532 nm laser was illuminated on the 10 nm semitransparent Au cathode. The photogenerated holes traveled through the MA<sub>3</sub>Bi<sub>2</sub>I<sub>9</sub> single crystals under applied bias to reach the other electrode. For the electron mobility measurements, a 532 nm laser was illuminated on the 10 nm semitransparent Au anode. The photogenerated electrons traveled through the MA<sub>3</sub>Bi<sub>2</sub>I<sub>9</sub> single crystals under applied bias until reaching the other electrode. The charge carrier transit time ( $t_{tr}$ ) was determined from the intercept of the pretransit and post-transit asymptotes of the photocurrent on a double logarithmic coordinate, as shown in Figs. S4–S7.

The mobility was calculated using the following formula:

$$\mu = \frac{d^2}{t_{tr}V}$$

where  $d$  is the thickness of the MA<sub>3</sub>Bi<sub>2</sub>I<sub>9</sub> single crystal,  $V$  the applied voltage,  $\mu$  the charge carrier mobility and  $t_{tr}$  the transit time of the charge carriers.

### 2.8. X-ray tube equipment and dose rate calibration

Two kinds of homemade X-ray tubes used in this work were developed and produced by the Institute of Fluid Physics, CAEP. A

relatively low-dose-rate (denoted by LDR) X-ray tube was used to study the detector performance. The LDR tube was designed for human medical X-ray CT with a small focal spot and excellent dose stability. The anode of the LDR tube is tungsten. The tube can be operated at voltages up to 140 kV, and the intrinsic filtration is equivalent to approximately 4.5 mm Al. Limited by the small focal spot, the LDR tube cannot continuously operate for a long period of time, especially at high X-ray dose rates.

A high-dose-rate (denoted by HDR) tube was used to study the radiation stability of the detector under continuous X-ray irradiation. The HDR tube was designed for X-ray irradiation research. The anode of the HDR tube is tungsten with cooling water, which can operate stably for several hours. The dose rate of the HDR tube can be adjusted by changing the tube current or distance between the detector and the tube. The highest dose rate can reach hundreds of  $\text{mGy}_{\text{air}} \text{min}^{-1}$ .

Dose rate calibrations of the tube were carried out by a Si dosimeter (model: RaySafe X2 R/F) from Fluke, which was operating in integrating mode. The dosimeter can monitor the voltage, exposure time and dose rate of the tube with excellent accuracy and stability. The dosimeter is calibrated annually by the National Institute of Measurement and Testing Technology by measuring the tube voltage and exposure time with a high-precision intervention high-voltage divider and time interval measuring instrument.

### 2.9. Photocurrent under X-ray exposure

The homemade LDR X-ray tube was used under an operating voltage of 100 kV. The dose rate was adjusted by changing the X-ray tube current as well as the location of the detector. The photocurrent of our Au/MA<sub>3</sub>Bi<sub>2</sub>I<sub>9</sub>/Au device was recorded using a low-noise current preamplifier (SR570, Stanford Research Systems) under different bias voltages, which were applied by a function generator (DS345, Stanford Research Systems) and a Keithley digital source meter (model 2400). The thicknesses of the MA<sub>3</sub>Bi<sub>2</sub>I<sub>9</sub> single crystal and identical Au electrodes on both sides of the crystal are approximately 2.5 mm and 80 nm, respectively. The  $\mu\tau$  product was fitted by the simplified Hecht equation:

$$J = J_0 \mu \tau V d^{-2} \left[ 1 - \exp\left(-\frac{d^2}{\mu \tau V}\right) \right]$$

where  $J$  is the photocurrent density,  $J_0$  is the saturated photocurrent density,  $V$  the applied bias and  $d$  the thickness of the single crystal.

### 2.10. X-ray response measurement

The devices with a configuration of Au/MA<sub>3</sub>Bi<sub>2</sub>I<sub>9</sub>/Au were fabricated in both in-plane and out-of-plane transport mode for X-ray detection measurements. The approximately 2.5-mm-thick MA<sub>3</sub>Bi<sub>2</sub>I<sub>9</sub> acted as the active layer, and the Au layers (80 nm) acted as the electrodes. The  $I$ - $t$  characteristics under various biases were measured by a low-noise current preamplifier (SR570, Stanford Research Systems). The homemade LDR X-ray tube was used as the X-ray source. The total X-ray dose was modulated by changing the current of the X-ray tube and the distance between the device and the X-ray source.

### 2.11. Stability characterization of the X-ray detector

The LDR tube was used to study the radiation stability of the detector under irradiation with an X-ray pulse (Fig. 4a, b). The HDR tube was used to study the radiation stability of the detector under continuous X-ray irradiation (Fig. 4c). MA<sub>3</sub>Bi<sub>2</sub>I<sub>9</sub> detectors without encapsulation working under different biases (50 and 100 V) were exposed to X-ray radiation under various dose rates (9.7, 38.2 and

152.8  $\text{mGy}_{\text{air}} \text{min}^{-1}$ ). The photocurrent was recorded during the X-ray radiation process.

### 2.12. Calculation of the signal-to-noise ratio

The signal current density ( $J_s$ ) was derived by subtracting the average photocurrent density ( $J_p$ ) by the average dark current density ( $J_d$ ) using  $J_s = J_p - J_d$ . The noise current density ( $J_n$ ) was obtained by calculating the standard deviation of the photocurrent density using the following expression:

$$J_n = \sqrt{\frac{1}{N} \sum_i^N (J_i - J_p)^2}$$

Then, the signal-to-noise ratio (SNR) was calculated by  $\text{SNR} = J_s / J_n$ .

Fig. S11 and Fig. 3b show the X-ray photoresponse characteristics of the in-plane device with a dose rate of  $425 \text{ nGy}_{\text{air}} \text{ s}^{-1}$  and the out-of-plane device with a dose rate of  $5.3 \text{ nGy}_{\text{air}} \text{ s}^{-1}$ . The  $J_s$  values were  $0.141 \text{ nA cm}^{-2}$  and  $0.053 \text{ nA cm}^{-2}$  for the in-plane and out-of-plane devices, respectively. The calculated average noise currents were  $0.014 \text{ nA cm}^{-2}$  and  $0.006 \text{ nA cm}^{-2}$ , resulting in SNR values of 9.8 and 8.8 for the in-plane and out-of-plane devices, respectively.

## 3. Results and discussion

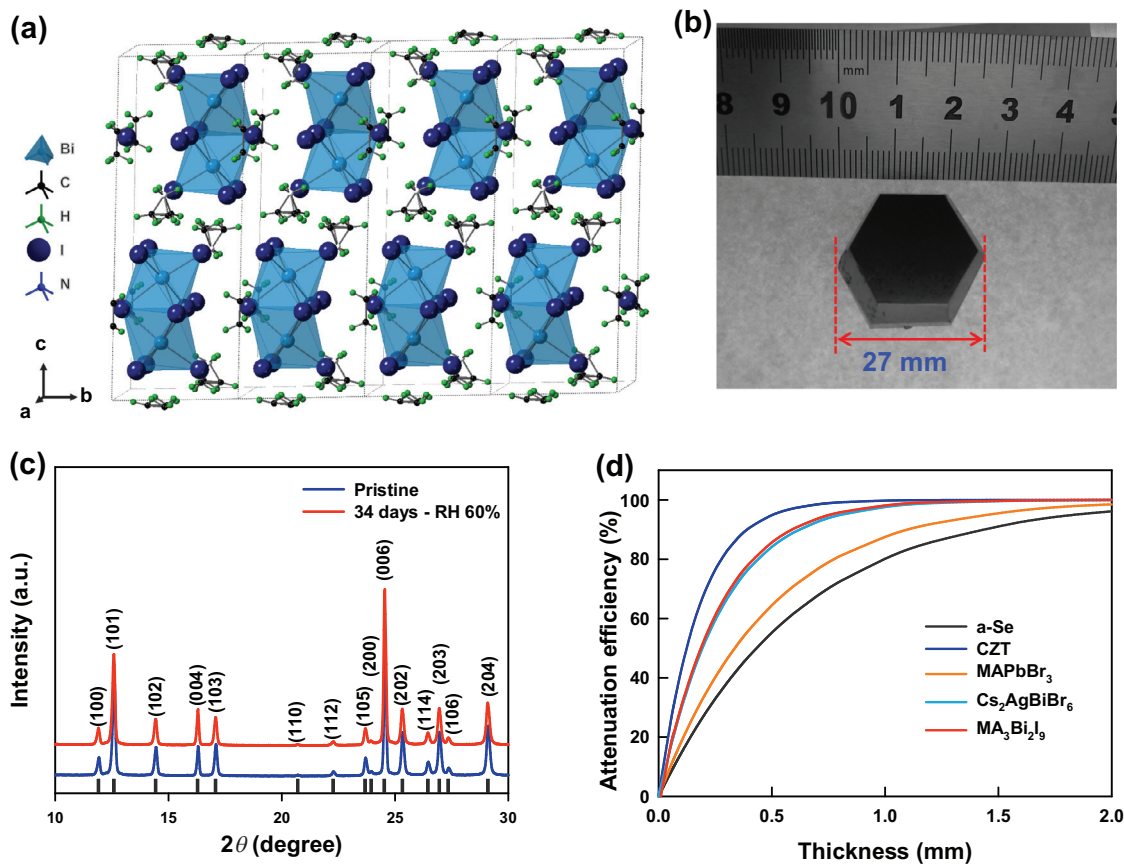
### 3.1. Development of zero-dimensional perovskite single crystals

We grew OD MA<sub>3</sub>Bi<sub>2</sub>I<sub>9</sub> perovskite single crystals using the seed-crystal-assisted constant-temperature evaporation method. MA<sub>3</sub>Bi<sub>2</sub>I<sub>9</sub> is a zero-dimensional material as illustrated in Fig. 1(a). The structure has hexagonal symmetry (P63/mmc) with face-sharing BiI<sub>6</sub> dioctahedral (Bi<sub>2</sub>I<sub>9</sub>)<sup>3-</sup> clusters isolated by MA<sup>+</sup>. Unit-cell parameters of  $a = b = 8.58 \text{ \AA}$  and  $c = 21.76 \text{ \AA}$  are derived from the XRD patterns. The organic cations act as insulating spacing layers between the (Bi<sub>2</sub>I<sub>9</sub>)<sup>3-</sup> clusters, and the unique zero-dimensional characteristics of MA<sub>3</sub>Bi<sub>2</sub>I<sub>9</sub> offer promise on suppressing ion migration. The as-grown MA<sub>3</sub>Bi<sub>2</sub>I<sub>9</sub> crystal is of hexagonal shape (Fig. 1b shows a crystal with  $\sim 27 \text{ mm} \times 23 \text{ mm} \times 13 \text{ mm}$  dimensions) and can endure temperatures up to  $250 \text{ }^\circ\text{C}$  with no phase transition (Fig. S1). The MA<sub>3</sub>Bi<sub>2</sub>I<sub>9</sub> perovskite crystals exhibited no observable change in the X-ray diffraction (XRD) patterns after storage for 34 days in ambient air with a RH of  $\sim 60\%$  (Fig. 1c).

The high-Z elements (Bi and I) and the high density ( $3.8 \text{ g cm}^{-3}$ ) favor a high X-ray absorption for MA<sub>3</sub>Bi<sub>2</sub>I<sub>9</sub> [8]. We compared the absorption coefficients (Fig. S2) and the attenuation efficiency of typical materials used for X-ray detection to 50 keV X-ray photons versus thickness (Fig. 1d). The absorption features of these materials were calculated according to the photon cross-section database [23]. The attenuation efficiency of MA<sub>3</sub>Bi<sub>2</sub>I<sub>9</sub> is similar to that of Cs<sub>2</sub>AgBiBr<sub>6</sub> and is larger than that of a-Se and MAPbBr<sub>3</sub>. We further measured the absorption spectra of a thin slice of MA<sub>3</sub>Bi<sub>2</sub>I<sub>9</sub> single crystal (Fig. S3), showing an optical band gap of 1.98 eV that lies in the range of room temperature operation for X-ray detectors [24].

### 3.2. Electronic properties of MA<sub>3</sub>Bi<sub>2</sub>I<sub>9</sub> single crystals

Although MA<sub>3</sub>Bi<sub>2</sub>I<sub>9</sub> exhibit zero dimensionality in crystalline structure, the MA<sub>3</sub>Bi<sub>2</sub>I<sub>9</sub> single crystals may exhibit anisotropy in electrical properties due to the different orientation arrangement of (Bi<sub>2</sub>I<sub>9</sub>)<sup>3-</sup> clusters along  $c$ -axis and  $a/b$ -axes. To investigate the anisotropic electrical properties of MA<sub>3</sub>Bi<sub>2</sub>I<sub>9</sub>, we cut the crystal into a rectangle along the  $c$  axis (Fig. 2a). We measured the



**Fig. 1.** Characterization of zero-dimensional (0D)  $\text{MA}_3\text{Bi}_2\text{I}_9$  perovskite single crystals. (a) Crystal structure of 0D  $\text{MA}_3\text{Bi}_2\text{I}_9$ . (b) Photograph of a  $\text{MA}_3\text{Bi}_2\text{I}_9$  crystal. (c) XRD patterns of pristine  $\text{MA}_3\text{Bi}_2\text{I}_9$  powders and aged powder kept under relative humidity (RH) of 60% for 34 days. (d) Calculated attenuation efficiencies of a-Se,  $\text{Cd}_{0.9}\text{Zn}_{0.1}\text{Te}$  (CZT),  $\text{MAPbBr}_3$ ,  $\text{Cs}_2\text{AgBiBr}_6$ , and  $\text{MA}_3\text{Bi}_2\text{I}_9$  semiconductors to 50 keV X-ray photons versus thickness.

in-plane (perpendicular to the  $c$  axis) resistivity and the out-of-plane (along the  $c$  axis) resistivity (Fig. 2b). The bulk resistivity in the out-of-plane direction reaches  $5.27 \times 10^{11} \Omega \text{ cm}$  and is approximately ten times higher than that in the in-plane direction ( $5.52 \times 10^{10} \Omega \text{ cm}$ ). The out-of-plane resistivity of  $\text{MA}_3\text{Bi}_2\text{I}_9$  crystal is considerably higher than that of CZT crystal ( $10^{10} \Omega \text{ cm}$ ) and other 3D perovskites ( $10^7$ – $10^8 \Omega \text{ cm}$ ) [25,26].

Hall-effect measurements were used to investigate the charge carrier mobility ( $\mu$ ) and dark carrier concentration in  $\text{MA}_3\text{Bi}_2\text{I}_9$  crystals (see Experimental section). A bulk resistivity of  $5 \times 10^{10} \Omega \text{ cm}$  was obtained, is similar to that observed in the in-plane direction.  $\text{MA}_3\text{Bi}_2\text{I}_9$  demonstrates p-type conduction with a mobility of  $70 \text{ cm}^2 \text{ V}^{-1} \text{ s}^{-1}$  and a carrier concentration of  $1.6 \times 10^6 \text{ cm}^{-3}$ . The mobility is slightly inferior to that of 3D Pb-based perovskites, while the carrier concentration is several orders of magnitude lower than those reported in 3D perovskites (typically  $\sim 10^{12} \text{ cm}^{-3}$ ) [27]. The low carrier concentration in  $\text{MA}_3\text{Bi}_2\text{I}_9$  can reduce the carrier scattering during the charge transporting process, which favors its high mobility.

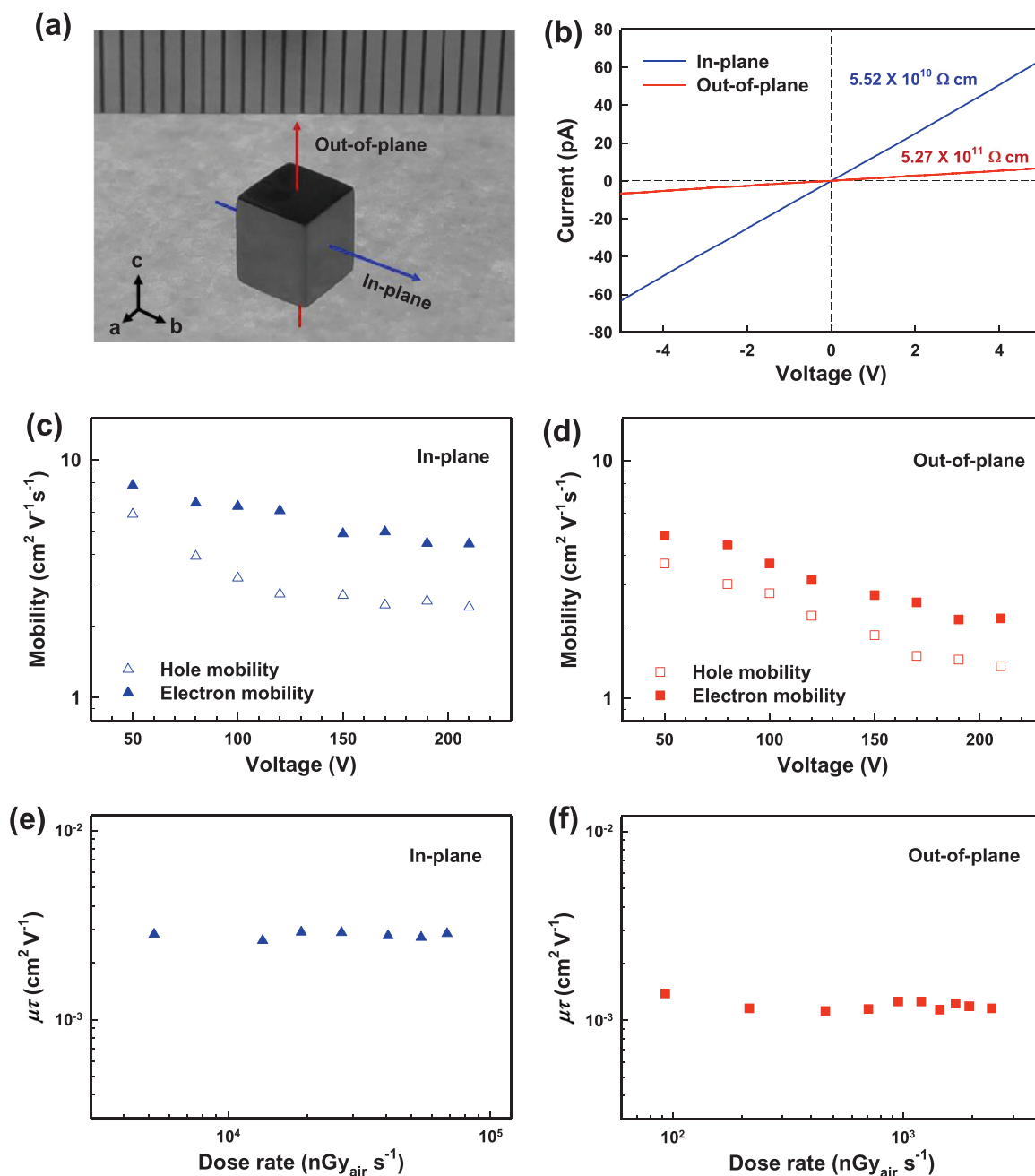
We further studied the charge carrier mobility ( $\mu$ ) of  $\text{MA}_3\text{Bi}_2\text{I}_9$  crystals by time-of-flight (TOF) at 50–210 V (Figs. S4–S7). The mobility shows a negative bias dependence due to the increased scattering at higher bias. The hole mobilities are 2–6  $\text{cm}^2 \text{ V}^{-1} \text{ s}^{-1}$  in the in-plane direction and 1–4  $\text{cm}^2 \text{ V}^{-1} \text{ s}^{-1}$  in the out-of-plane direction, and the electron mobilities are 4–8  $\text{cm}^2 \text{ V}^{-1} \text{ s}^{-1}$  in the in-plane direction and 2–5  $\text{cm}^2 \text{ V}^{-1} \text{ s}^{-1}$  in the out-of-plane direction (Fig. 2c, d). The quasi-balanced carrier mobilities indicate ambipolar transport in  $\text{MA}_3\text{Bi}_2\text{I}_9$  crystals. We further derived the dark free carrier concentration ( $n$ ) in the  $\text{MA}_3\text{Bi}_2\text{I}_9$  crystal through

$n = 1/\rho q\mu$ , where  $\rho$  is the bulk resistivity and  $q$  is the elementary charge. The carrier concentration in  $\text{MA}_3\text{Bi}_2\text{I}_9$  crystals lies within the range from  $10^6$ – $10^7 \text{ cm}^{-3}$  (Table S2). The mobility and carrier concentration show a little difference with the data obtained using Hall-effect measurements, but once again demonstrates the high mobility and low carrier concentration features of  $\text{MA}_3\text{Bi}_2\text{I}_9$  crystals.

We then measured the charge carrier mobility-lifetime ( $\mu\tau$ ) product in  $\text{MA}_3\text{Bi}_2\text{I}_9$  under various bias using photoconductivity method (Fig. S8). We employed a modified Hecht equation to fit the photoconductivity curve under X-ray excitation to obtain the  $\mu\tau$  values (see Experimental section) [28]. The  $\mu\tau$  products of  $2.8 \times 10^{-3}$  and  $1.2 \times 10^{-3} \text{ cm}^2 \text{ V}^{-1}$  were obtained for the in-plane and the out-of-plane directions, respectively (Fig. 2e, f). The  $\mu\tau$  products in both directions are superior to those of CZT and  $\text{HgI}_2$  semiconductors [25,29].

### 3.3. Performance of X-ray detectors

We fabricated direct-conversion X-ray detectors and characterized their performance using a device structure of  $\text{Au}/\text{MA}_3\text{Bi}_2\text{I}_9$  single crystal/ $\text{Au}$ . The dark current density ( $J_d$ ) plays a crucial role on the sensitivity and LoD of X-ray detectors. We measured the  $J_d$  of the  $\text{Au}/\text{MA}_3\text{Bi}_2\text{I}_9/\text{Au}$  X-ray detectors (Fig. 3a). The  $J_d$  in the out-of-plane direction is  $0.98 \text{ nA cm}^{-2}$  under an applied bias of 120 V, which is lower than that in the in-plane direction ( $28.4 \text{ nA cm}^{-2}$ ). The  $J_d$  maintained constant during the measurements and no obvious current drift was observed in either out-of-plane or in-plane direction (Fig. S9a, b). The stable outputs of  $J_d$  in-

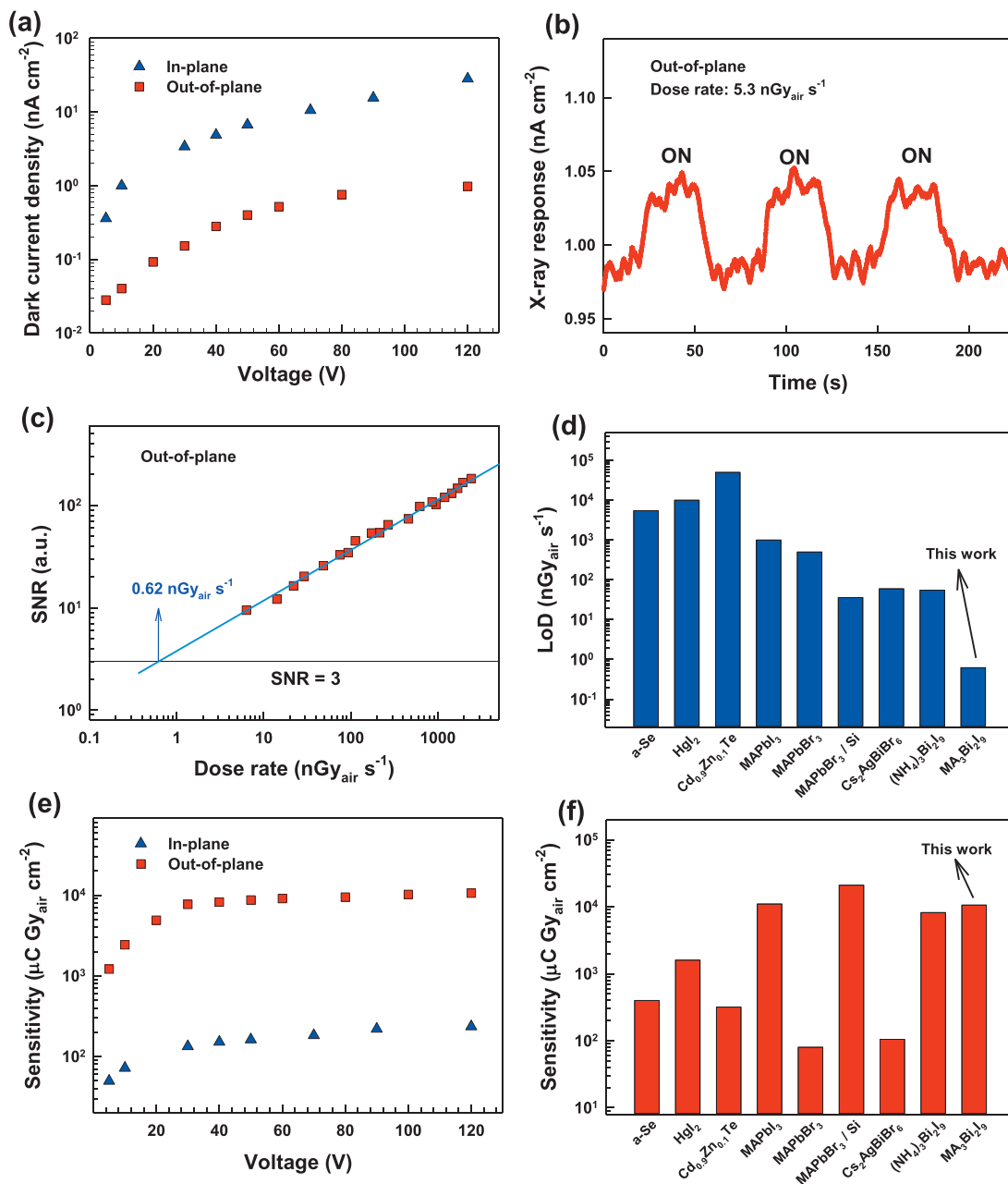


**Fig. 2.** Anisotropic electronic properties of MA<sub>3</sub>Bi<sub>2</sub>I<sub>9</sub> single crystals. (a) Photograph of the MA<sub>3</sub>Bi<sub>2</sub>I<sub>9</sub> single crystal after cutting and polishing; charge transport perpendicular to the *c* axis in hexagonal MA<sub>3</sub>Bi<sub>2</sub>I<sub>9</sub> was defined as in-plane and charge transport along the *c* axis was defined as out-of-plane. (b) Anisotropic resistivity of the MA<sub>3</sub>Bi<sub>2</sub>I<sub>9</sub> single crystal. (c, d) Charge carrier mobility in MA<sub>3</sub>Bi<sub>2</sub>I<sub>9</sub> single crystal of (c) in-plane and (d) out-of-plane measured by time-of-flight (TOF) technique. (e, f) Dose rate dependence of the charge carrier mobility-lifetime ( $\mu\tau$ ) product for MA<sub>3</sub>Bi<sub>2</sub>I<sub>9</sub> single crystal in (e) in-plane and (f) out-of-plane transport mode.

dicates that ion migration in 0D MA<sub>3</sub>Bi<sub>2</sub>I<sub>9</sub> crystals is negligible in both directions. We evaluated the ionic conduction activation energy ( $E_a$ ) by temperature-dependent conductivity measurements [30,32], and the  $E_a$  values were fitted to be 0.31 and 0.46 eV for the in-plane and out-of-plane directions, respectively (Fig. S10), higher than those reported for 3D MAPbI<sub>3</sub> and MAPbBr<sub>3</sub> (typically below 0.19 eV) [26,32].

The low and stable dark current enables us to observe stable and distinguishable signals in response to low X-ray radiation. When exposed to a dose rate of 5.3 nGy<sub>air</sub> s<sup>-1</sup>, the lowest value achievable in our X-ray generator, the out-of-plane devices exhibit a signal-to-noise ratio (SNR) of 8.8 (Fig. 3b, see Experimental

section for details). The LoD of 0.62 nGy<sub>air</sub> s<sup>-1</sup> was linearly extrapolated from the X-ray dose rate-dependent SNR following the IUPAC standard with a SNR value of 3 (Fig. 3c). This LoD represents the lowest value reported for X-ray detectors (the lowest LoD reported previously was 36 nGy<sub>air</sub> s<sup>-1</sup> for direct-conversion X-ray detectors; Fig. 3(d), Table S1) [1,2,13,26,30,31,33]. Notably, the LoD of 0.62 nGy<sub>air</sub> s<sup>-1</sup> for the out-of-plane devices approaches the background radiation on Earth (~0.1 nGy<sub>air</sub> s<sup>-1</sup>) [11], and it is approximately 8,800 times lower than the dose rate required for X-ray diagnostics used currently (5.5 μGy<sub>air</sub> s<sup>-1</sup>) [33], offering the potential to further lower the radiation dose required for medical radiography, industrial inspection and security scanning.

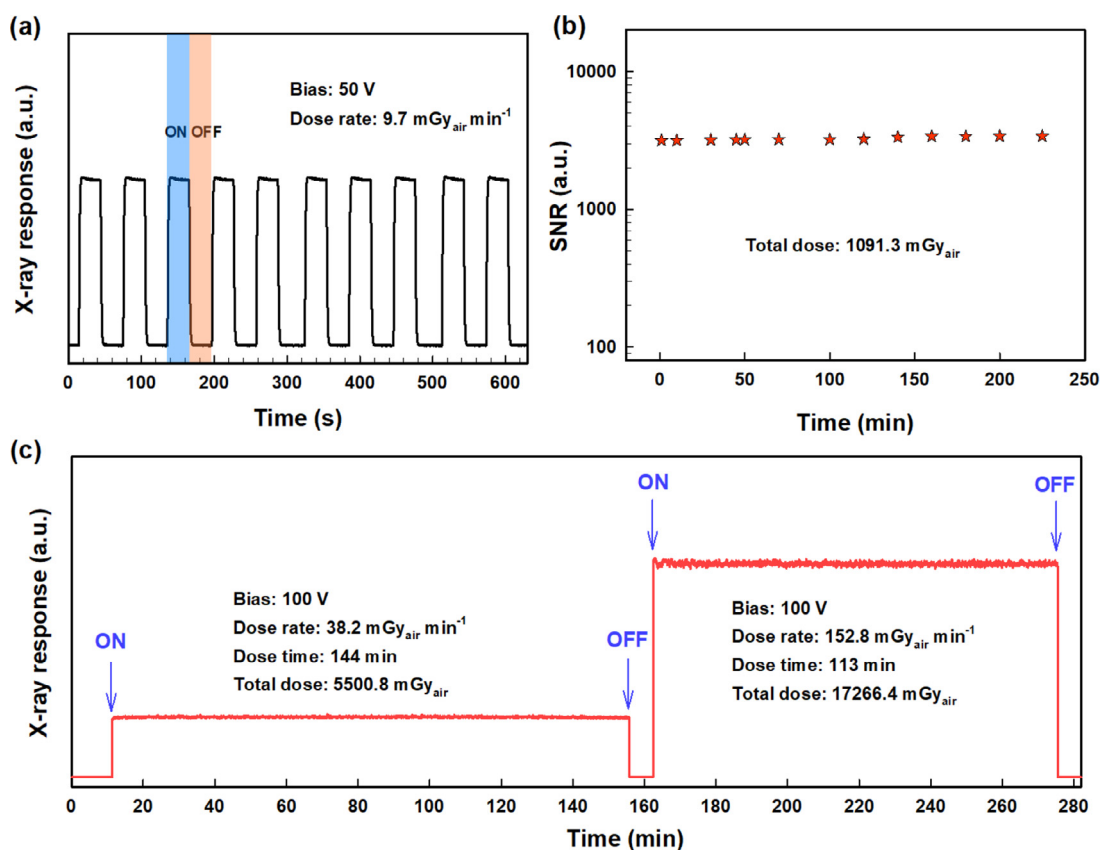


**Fig. 3.** Performance of MA<sub>3</sub>Bi<sub>2</sub>I<sub>9</sub> X-ray detectors. (a) Bias dependence of the dark current density ( $J_d$ ) of Au/MA<sub>3</sub>Bi<sub>2</sub>I<sub>9</sub>/Au device. (b) X-ray response characteristics for an out-of-plane device with a dose rate of 5.3 nGy<sub>air</sub> s<sup>-1</sup>. (c) X-ray dose rate-dependent signal-to-noise ratio (SNR) of the out-of-plane device (40 V bias). The LoD of 0.62 nGy s<sup>-1</sup> is derived from the slope of the fitting line with a signal-to-noise ratio of 3. (d) Comparison of LoD of various direct-conversion X-ray detectors [1,2,13,26,30,31]. (e) Bias-dependent X-ray sensitivity of the in-plane and out-of-plane devices. (f) Comparison of the best sensitivity in literature for direct-conversion X-ray detectors [1,2,13,26,30,31].

Fig. 3e presents the X-ray sensitivity of the in-plane and out-of-plane devices under various biases. The out-of-plane devices have a X-ray sensitivity of 10,620  $\mu\text{C Gy}_{\text{air}}^{-1} \text{cm}^{-2}$  at the operating bias of 120 V, which is about 50 times higher than the sensitivity in the in-plane devices. The out-of-plane sensitivity is comparable to the best values obtained by 3D perovskite ( $1.1 \times 10^4 \mu\text{C Gy}_{\text{air}}^{-1} \text{cm}^{-2}$  for MAPbI<sub>3</sub> and  $2.1 \times 10^4 \mu\text{C Gy}_{\text{air}}^{-1} \text{cm}^{-2}$  for hybrid MAPbBr<sub>3</sub>/Si) and 2D perovskite ( $8,400 \mu\text{C Gy}_{\text{air}}^{-1} \text{cm}^{-2}$  for (NH<sub>4</sub>)<sub>3</sub>Bi<sub>2</sub>I<sub>9</sub>) X-ray detectors, but is higher than those of a-Se, CZT and Cs<sub>2</sub>AgBiBr<sub>6</sub> (Fig. 3f, Table S1). It is worth noting that, unlike 2D hybrid Bi halide perovskites cannot achieved low LoD and high sensitivity in the same direction [30], OD MA<sub>3</sub>Bi<sub>2</sub>I<sub>9</sub> X-ray detectors achieve simultaneously low LoD and high X-ray sensitivity in the same out-of-plane transport mode.

#### 3.4. Operational stability of X-ray detectors

We finally investigated the operational stability of MA<sub>3</sub>Bi<sub>2</sub>I<sub>9</sub> X-ray detectors (in the out-of-plane direction) under ambient condition without encapsulation. The device was first exposed to X-ray radiation with a dose rate of 9.7 mGy<sub>air</sub> min<sup>-1</sup> under a constant bias of 50 V for 225 pulses (Fig. 4a). Following a total X-ray dose of 1091.3 mGy<sub>air</sub>, no observable change in SNR occurred in the detector (Fig. 4b). We then applied a higher working bias (100 V) and higher continuous X-ray dose rates (38.2 and 152.8 mGy<sub>air</sub> min<sup>-1</sup>) to irradiate the detector, and no obvious change in photocurrent was found following an additional total X-ray dose of over 22,767.2 mGy<sub>air</sub> (Fig. 4c). This total dose is equivalent to ~230,000 times of the dose required for an X-ray chest



**Fig. 4.** Radiation stability of OD MA<sub>3</sub>Bi<sub>2</sub>I<sub>9</sub> X-ray detectors (out-of-plane). (a, b) Device operational stability under X-ray pulses with a time interval of 30 s: (a) A portion of the device responses to X-ray pulses and (b) time-dependent SNR of the devices. (c) Device operational stability against continuous X-ray irradiation with high dose rates under a high bias voltage of 100 V. Radiation stability tests were performed in ambient air without encapsulation.

radiograph (typically  $\sim 0.1$  mGy<sub>air</sub> for commercial instruments). This indicates that X-detectors using OD MA<sub>3</sub>Bi<sub>2</sub>I<sub>9</sub> perovskites can guarantee reliable operation for medical radiography applications.

#### 4. Conclusions

In summary, the OD MA<sub>3</sub>Bi<sub>2</sub>I<sub>9</sub> perovskite single crystal presents high attenuation efficiency, a high  $\mu\tau$  product, an ultralow carrier concentration, suppressed ion migration, and excellent thermal and ambient stability. These features endow the MA<sub>3</sub>Bi<sub>2</sub>I<sub>9</sub> devices with ultrasensitive and high stability X-ray detection. The X-ray detection limit of the MA<sub>3</sub>Bi<sub>2</sub>I<sub>9</sub> detectors down to 0.62 nGy<sub>air</sub> s<sup>-1</sup> enables a reduction in the dosage required for regular X-ray inspection to a low level, enabling reduced health risks and more frequent diagnostic imaging assays. Moreover, the excellent operational stability under high bias and high X-ray dose more than 23,858.5 mGy<sub>air</sub> reveals its great value in practical application. Our results pave a way of exploring ultrasensitive and stable X-ray detectors.

#### Author contributions

X.Z. and W-H.Z. conceived the idea and designed the experiments. W-H.Z., and J.L. led the collaboration efforts. P.W. prepared the perovskite single crystals. X.Z. and T.S. performed the structural and optoelectronic characterization of the perovskites. H.T. and M.I.S. helped on the growth of single crystals and characterization. X.Z. and T.S. fabricated the detector. W.Z., X.Z. designed and carried out the detector performance characterization with the supervision of J.L. W.Z., S.T. and L.C. carried out the stability characterization. Y. P. and W.Z. prepared the X-ray sources and carried

out the dose calibrations. X.Z., H.T., W.Z., M.I.S. and W-H.Z. wrote the manuscript. All authors discussed the results and commented on the manuscript.

#### Declaration of competing interests

The authors declared that they have no conflicts of interest to this work.

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#### Data availability

The data sets analyzed during the study are available from the corresponding authors upon request. Correspondence and requests for materials should be addressed to W-H. Z. (whzhang@caep.cn) or J.L. (longjidong@tsinghua.org.cn).

#### Supplementary materials

Supplementary materials associated with this article can be found, in the online version, at doi:[10.1016/j.jechem.2020.02.049](https://doi.org/10.1016/j.jechem.2020.02.049).

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